



Session Title:	[WeA1] Gallium Oxides
Session Date:	July 15 (Wed.), 2026
Session Time:	10:25-12:10
Session Room:	Room A (Baekrok Hall B-1, 1F)
Session Chairs	

[WeA1-1] [Invited]	10:25-10:55
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TBA

Vanya Darakchieva, Lund University, Sweden

[WeA1-2]	10:55-11:10
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Effects and Applications of Nuclear Radiation in Ga₂O₃

Yoonho Choi, Jaeheon Jung, Hae Seong Hwang, and Roy B. Chung, Kyungpook National University, Korea

[WeA1-3]	11:10-11:25
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AlN Mesa Sidewall Passivation Enables Thermally Stable Reverse Blocking in Vertical β -Ga₂O₃ Power Diodes

Ganesh Mainali, Nuzhat Yousf, Dhanu Chettri, Haicheng Cao, Leo Raj Solay, and Xiaohang Li, King Abdullah University of Science and Technology, Kingdom of Saudi Arabia

[WeA1-4]	11:25-11:40
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High Efficiency Growth of (001) β -Ga₂O₃ Films by Cold-Wall MOCVD

Shun Ukita and Hironori Okumura, University of Tsukuba, Japan

[WeA1-5]	11:40-11:55
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Heteroepitaxial Growth of β -Ga₂O₃ on High-Angle Off-Cut Sapphire via MOCVD

Ji-Hyeon Park, Hyeong-Yun Kim, JungHun Choi, and Dae-Woo Jeon, Korea Institute of Ceramic Engineering and Technology, Korea

[WeA1-6]	11:55-12:10
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Influence of Substrate Atomic Symmetry on the Epitaxy and Rotational Domain Formation of κ -Ga₂O₃

Ha Young Kang, Jaeheon Jung, Young Soo Hwang, and Roy B. Chung, Kyungpook National University, Korea